One step fabrication of GaAs nanowires via anodization and their application as Infrared Photodetectors.

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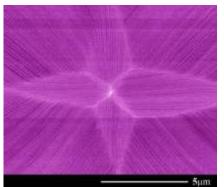
Development of advanced technologies for obtaining of semiconductor nanomatrix and other low dimensions semiconductor nanostructures

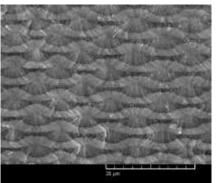
Semiconductor nanotemplates based on semiconductor

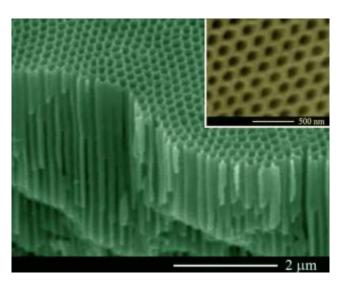
compounds such as: InP(Eg = 1.3 eV at 300 K); GaAs(1.4 eV);

CdSe (1.7eV); GaP (2.4 eV); ZnSe (2.7 eV), GaN (3.4 eV)

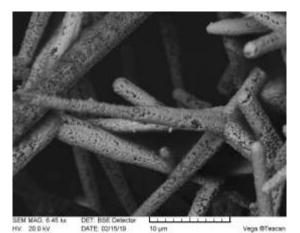
Material Nanostructuring by Design

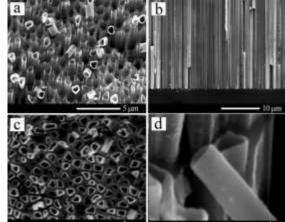


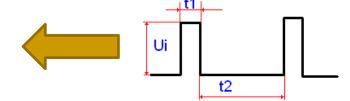




Nanocomposite materials metal/ semiconductor

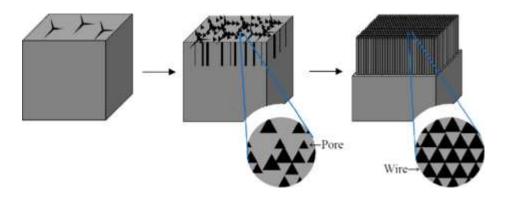




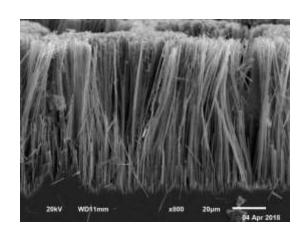


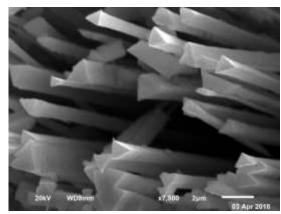
Pulsed electrochemical deposition

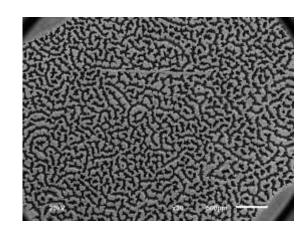
Electrochemical nanostructuring of GaAs: from porous to 1D nanostructures



Schematic representation of formation of GaAs nanowire arrays

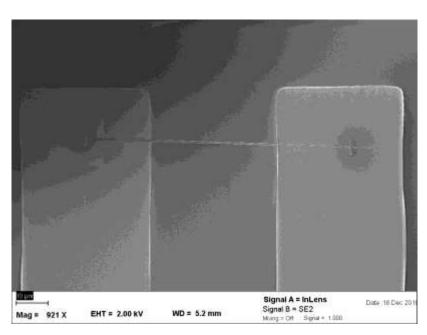




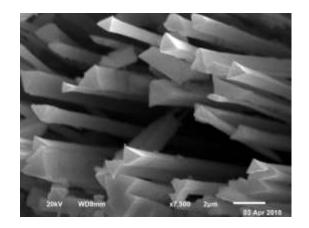


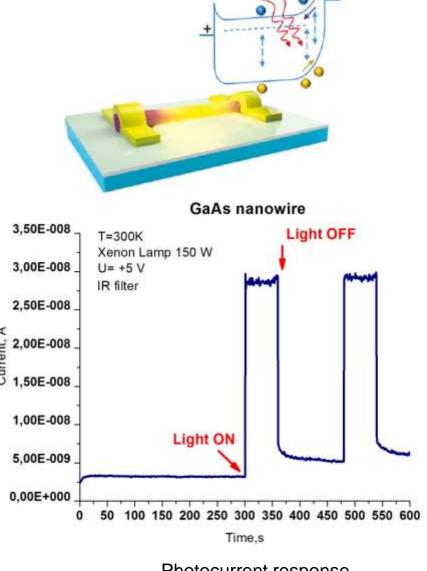
- Cost-effective
- Accessible
- Environmentally friendly (nanostructuring in NaCl)

Photosensibility study of GaAs nanowires



SEM image of GaAs nanowire contacted with FIB



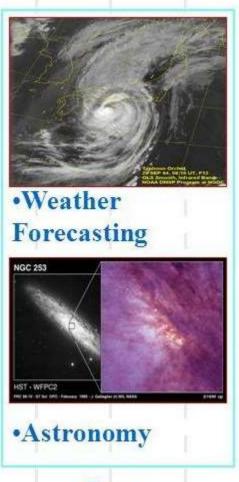


Infrared light

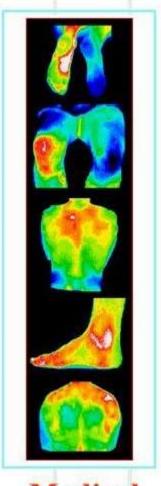
Applications of IR Detectors Arrays







Space



Medical



Night vision



•Infrared target detection

Military

- Missile tracking
- Environmental sensing

Thank you for attention